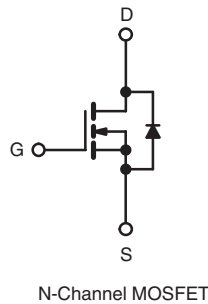
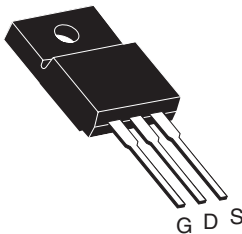


Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	400	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10$ V	0.55
Q_g (Max.) (nC)	39	
Q_{gs} (nC)	10	
Q_{gd} (nC)	19	
Configuration	Single	

TO-220 FULLPAK

FEATURES

- Ultra Low Gate Charge
- Reduced Gate Drive Requirement
- Enhanced 30 V V_{GS} Rating
- Isolated Package
- High Voltage Isolation = 2.5 kV_{RMS} (t = 60 s, f = 60 Hz)
- Sink to Lead Creepage Distance = 4.8 mm
- Repetitive Avalanche Rated
- Lead (Pb)-free Available


DESCRIPTION

This new series of low charge Power MOSFETs achieve significantly lower gate charge over conventional MOSFETs. Utilizing advanced Power MOSFETs technology, the device improvements allow for reduced gate drive requirements, faster switching speeds and increased total system savings. These device improvements combined with the proven ruggedness and reliability that are characteristic of Power MOSFETs offer the designer a new standard in power transistors for switching applications. The TO-220 Fullpak eliminates the need for additional insulating hardware. The moulding compound used provides a high isolation capability and low thermal resistance between the tab and external heatsink.

ORDERING INFORMATION	
Package	TO-220 FULLPAK
Lead (Pb)-free	IRFI740GLCPbF
	SiHFI740GLC-E3
SnPb	IRFI740GLC
	SiHFI740GLC

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V_{DS}	400	V	
Gate-Source Voltage	V_{GS}	± 30		
Continuous Drain Current	V_{GS} at 10 V	$T_C = 25$ °C	5.7	A
		$T_C = 100$ °C	3.6	
Pulsed Drain Current ^a	I_{DM}	23		
Linear Derating Factor		0.32	W/°C	
Single Pulse Avalanche Energy ^b	E_{AS}	310	mJ	
Repetitive Avalanche Current ^a	I_{AR}	5.7	A	
Repetitive Avalanche Energy ^a	E_{AR}	4.0	mJ	
Maximum Power Dissipation	$T_C = 25$ °C	P_D	40	W
Peak Diode Recovery dV/dt^c		dV/dt	4.0	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	°C	
Soldering Recommendations (Peak Temperature)	for 10 s	300 ^d		
Mounting Torque	6-32 or M3 screw		10	lbf · in
			1.1	N · m

Notes

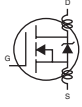
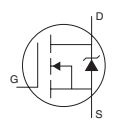
- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, L = 16 mH, $R_G = 25$ Ω , $I_{AS} = 5.7$ A (see fig. 12).
- $I_{SD} \leq 10$ A, $dI/dt \leq 120$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	65	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	3.1	

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	400	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$	-	0.76	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}$	-	-	25	μA
		$V_{DS} = 320\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ $I_D = 3.4\text{ A}^b$	-	-	0.55	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 6.0\text{ A}^b$	3.0	-	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 1.0\text{ MHz}$, see fig. 5	-	1100	-	pF
Output Capacitance	C_{oss}		-	190	-	
Reverse Transfer Capacitance	C_{rss}		-	18	-	
Drain to Sink Capacitance	C	$f = 1.0\text{ MHz}$	-	12	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$ $I_D = 10\text{ A}, V_{DS} = 320\text{ V},$ see fig. 6 and 13 ^b	-	-	39	nC
Gate-Source Charge	Q_{gs}		-	-	10	
Gate-Drain Charge	Q_{gd}		-	-	19	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 200\text{ V}, I_D = 10\text{ A},$ $R_G = 9.1\text{ }\Omega, R_D = 20\text{ }\Omega,$ see fig. 10 ^b	-	11	-	ns
Rise Time	t_r		-	31	-	
Turn-Off Delay Time	$t_{d(off)}$		-	25	-	
Fall Time	t_f		-	20	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	5.7	A
Pulsed Diode Forward Current ^a	I_{SM}		-	-	23	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 5.7\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	2.0	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$	-	380	570	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	2.8	4.2	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

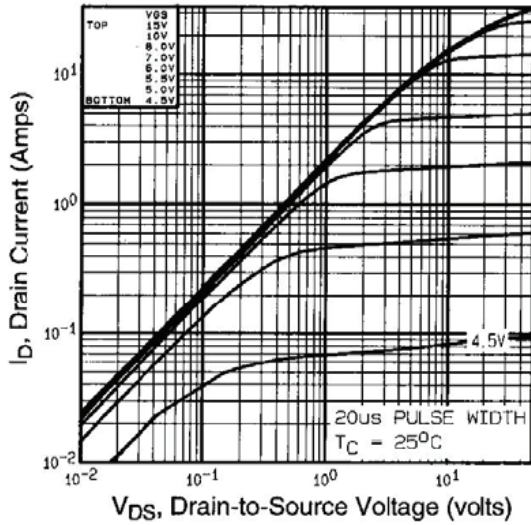


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

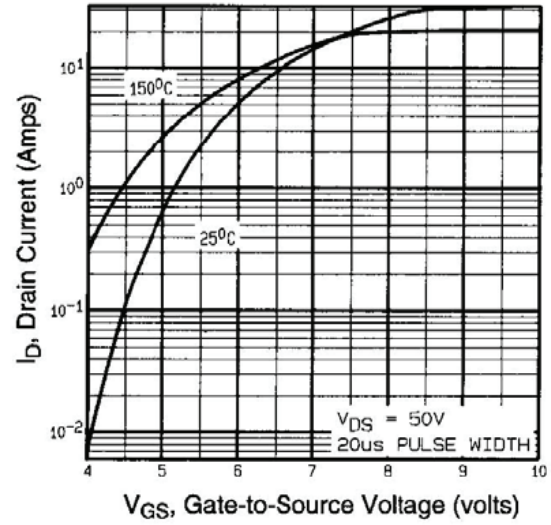


Fig. 3 - Typical Transfer Characteristics

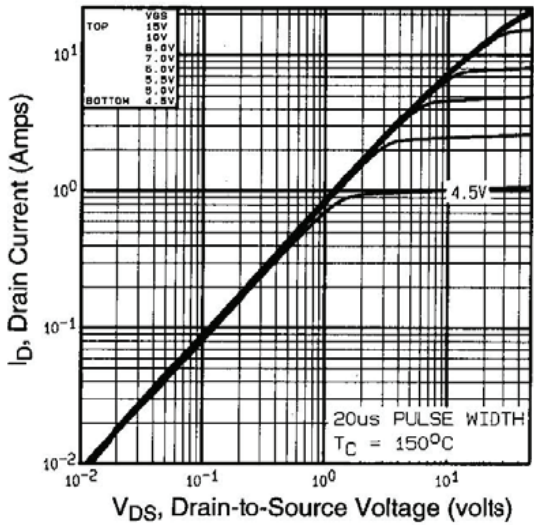


Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

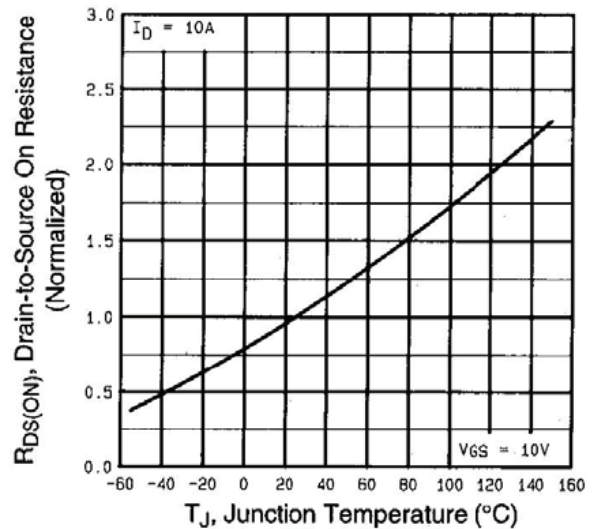


Fig. 4 - Normalized On-Resistance vs. Temperature

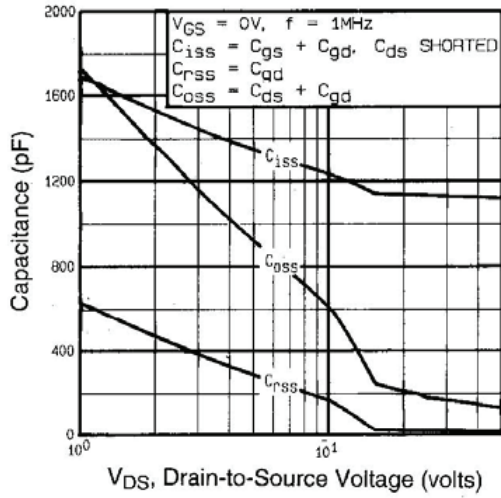


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

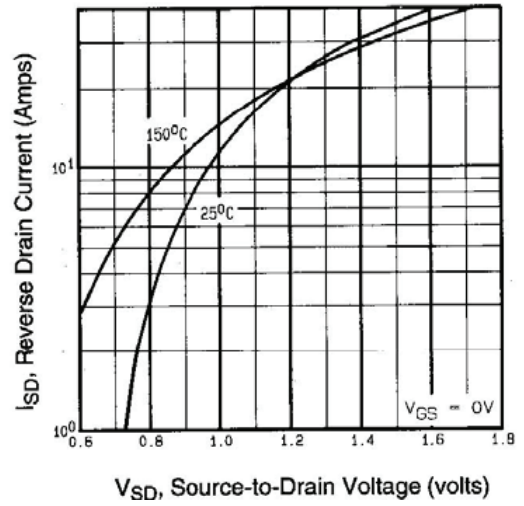


Fig. 7 - Typical Source-Drain Diode Forward Voltage

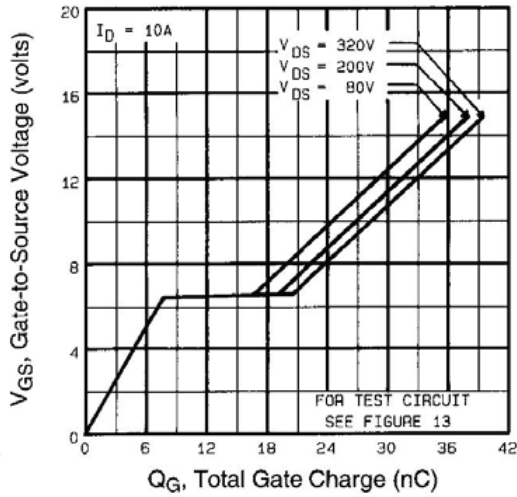


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

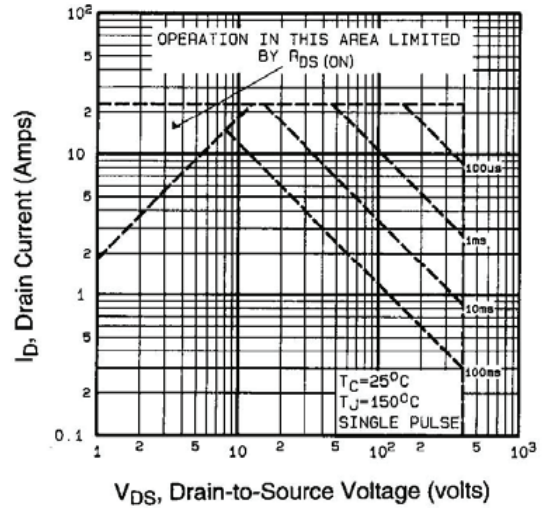


Fig. 8 - Maximum Safe Operating Area

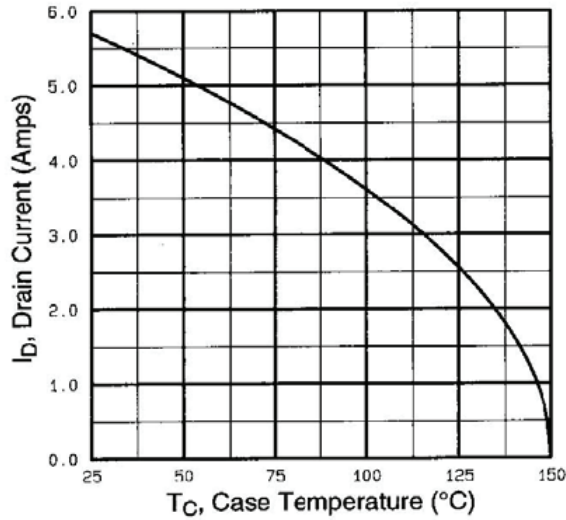


Fig. 9 - Maximum Drain Current vs. Case Temperature

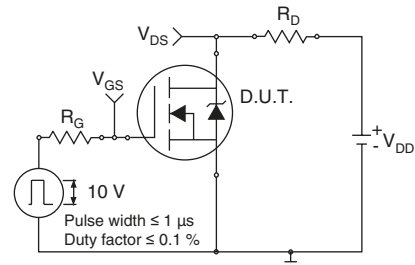


Fig. 10a - Switching Time Test Circuit

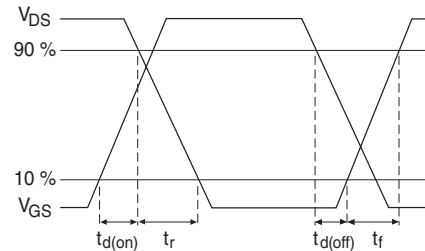


Fig. 10b - Switching Time Waveforms

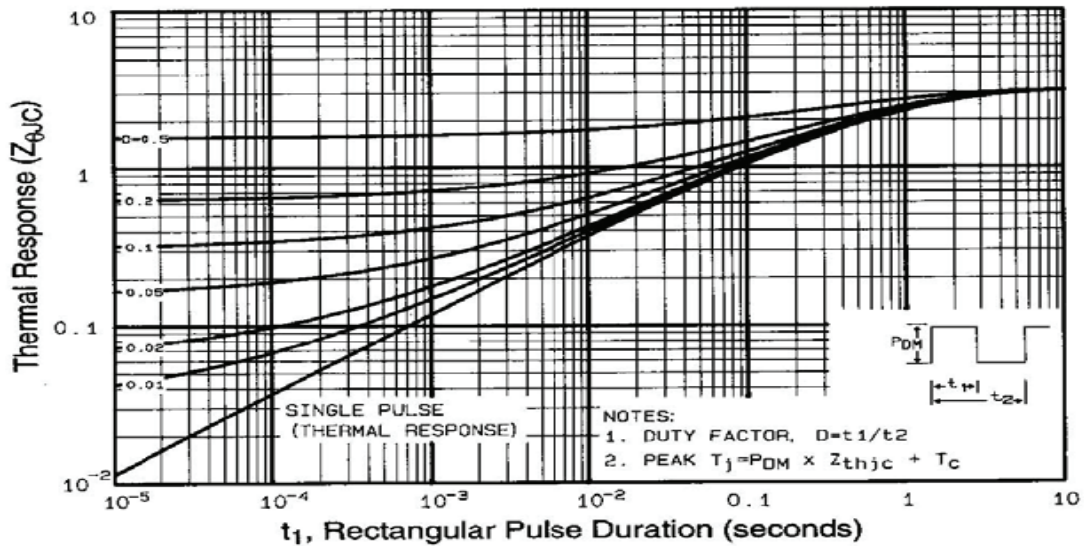


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

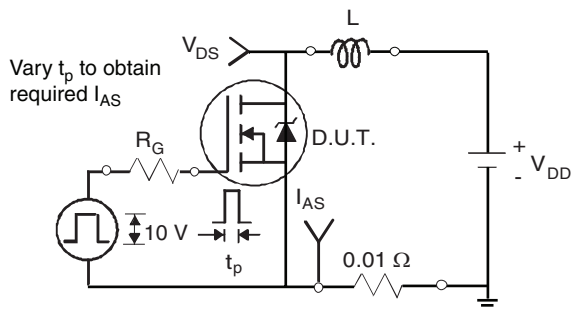


Fig. 12a - Unclamped Inductive Test Circuit

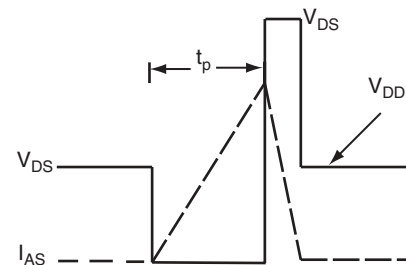


Fig. 12b - Unclamped Inductive Waveforms

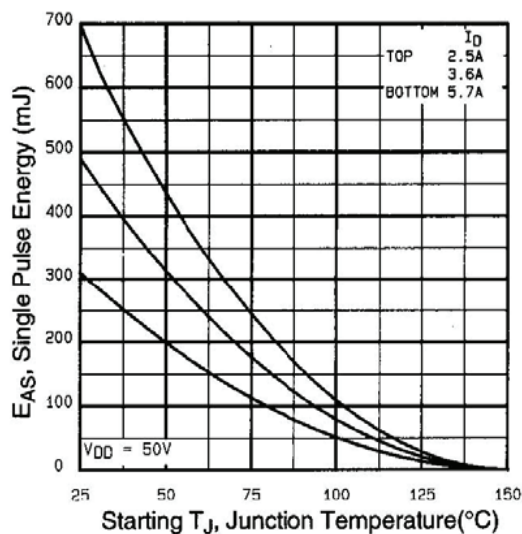


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

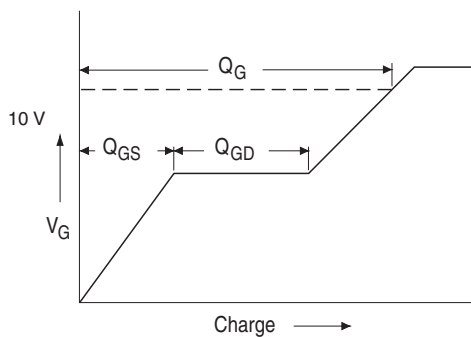


Fig. 13a - Basic Gate Charge Waveform

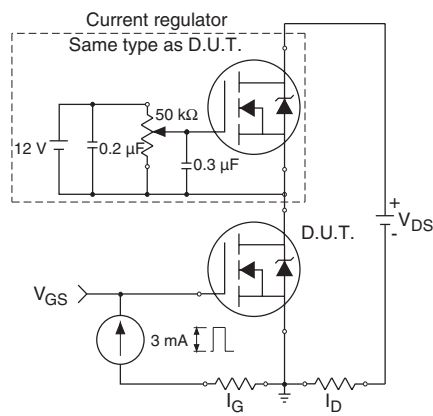
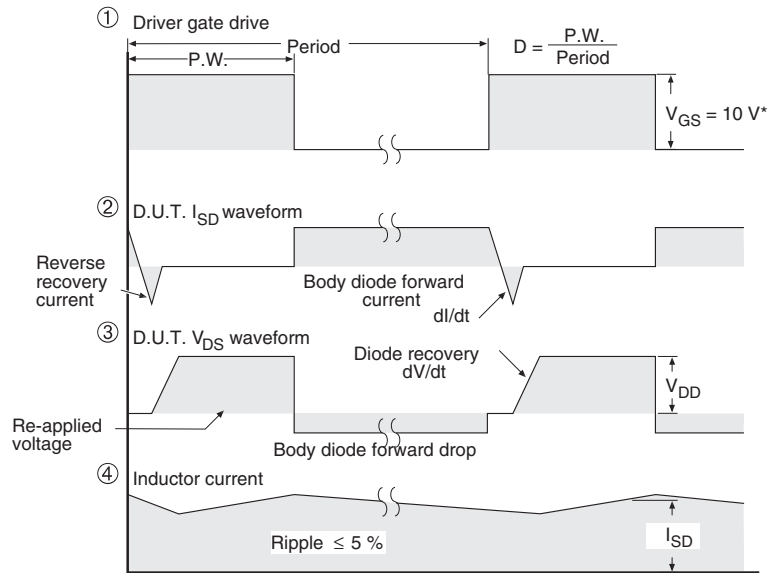
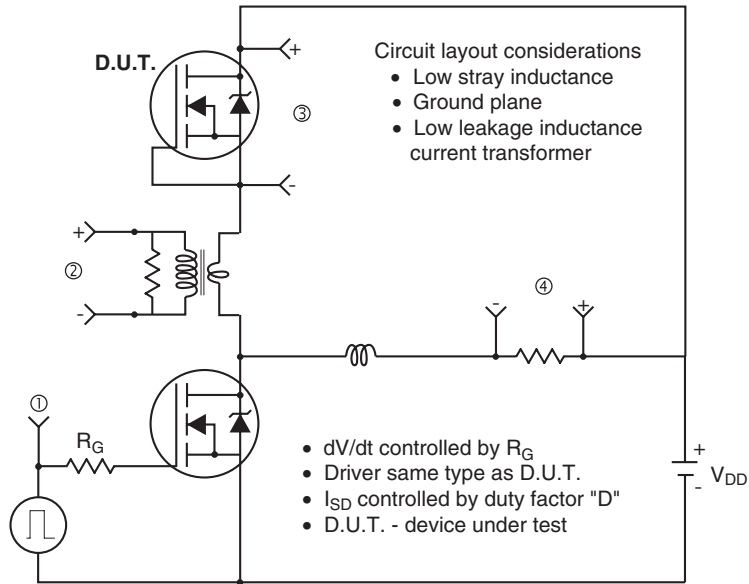


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

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